

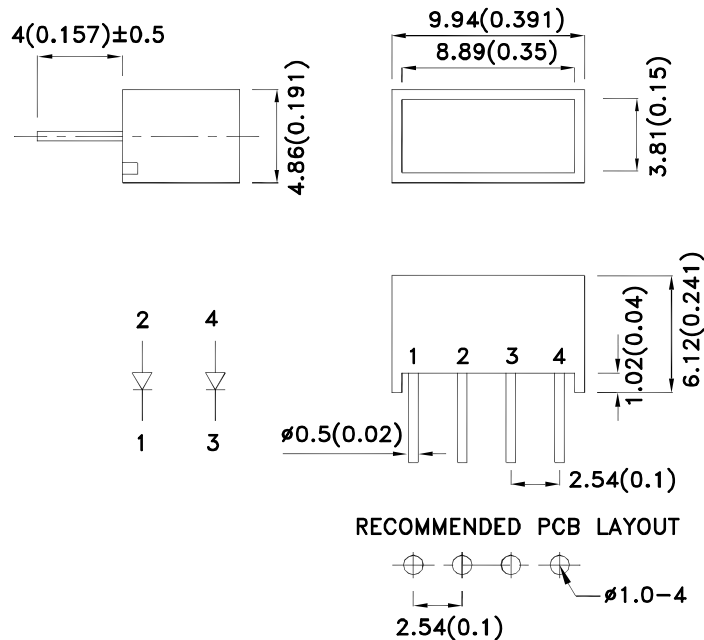
### Features

- Uniform light emitting area.
- Low current operation.
- Easily mounted on P.C. boards.
- Flush mountable.
- Can be used with panels and legend mounts.
- RoHS compliant.

### Description

The Hyper Red source color devices are made with Al-GaN on GaAs substrate Light Emitting Diode.

### Package Dimensions & Internal Circuit Diagram



Notes:

1. All dimensions are in millimeters (inches), Tolerance is  $\pm 0.25(0.01)$  unless otherwise noted.
2. The specifications, characteristics and technical data described in the datasheet are subject to change without prior notice.



## Selection Guide

Part No.	Dice	Lens Type	Iv (mcd) [1] @ 20mA	
			Min.	Typ.
KB-A100SURKW	Hyper Red (AlGaInP)	White Diffused	120	230

Note:

- Luminous intensity/ luminous Flux: +/-15%.

## Electrical / Optical Characteristics at TA=25°C

Symbol	Parameter	Device	Typ.	Max.	Units	Test Conditions
$\lambda_{peak}$	Peak Wavelength	Hyper Red	650		nm	I <sub>F</sub> =20mA
$\lambda_D$ [1]	Dominant Wavelength	Hyper Red	630		nm	I <sub>F</sub> =20mA
$\Delta\lambda_{1/2}$	Spectral Line Half-width	Hyper Red	28		nm	I <sub>F</sub> =20mA
C	Capacitance	Hyper Red	35		pF	V <sub>F</sub> =0V;f=1MHz
V <sub>F</sub> [2]	Forward Voltage	Hyper Red	1.95	2.5	V	I <sub>F</sub> =20mA
I <sub>R</sub>	Reverse Current	Hyper Red		10	uA	V <sub>R</sub> =5V

Notes:

- Wavelength: +/-1nm.
- Forward Voltage: +/-0.1V.

## Absolute Maximum Ratings at TA=25°C

Parameter	Hyper Red	Units
Power dissipation	75	mW
DC Forward Current	30	mA
Peak Forward Current [1]	185	mA
Reverse Voltage	5	V
Operating / Storage Temperature	-40°C To +85°C	
Lead Solder Temperature[2]	260°C For 3-5 Seconds	

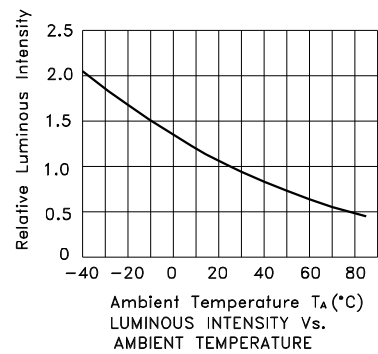
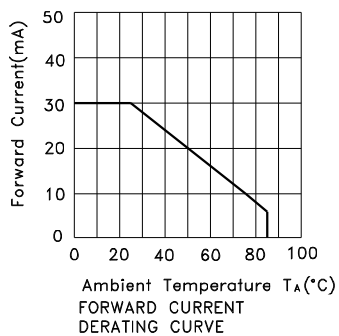
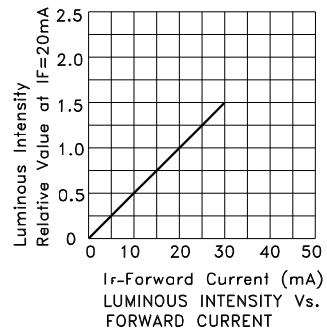
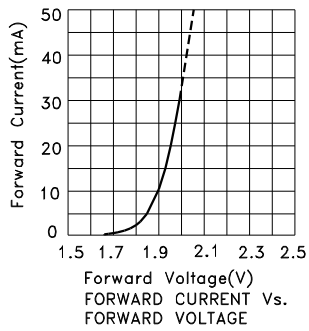
Notes:

- 1/10 Duty Cycle, 0.1ms Pulse Width.
- 2mm below package base.



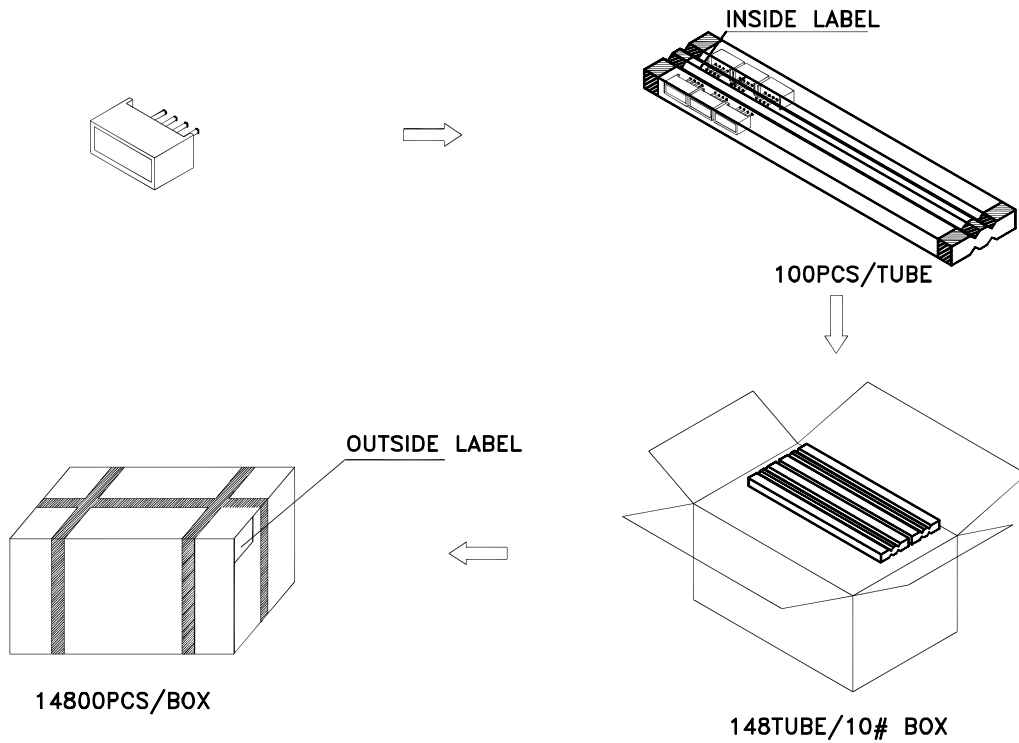
## Hyper Red

### KB-A100SURKW

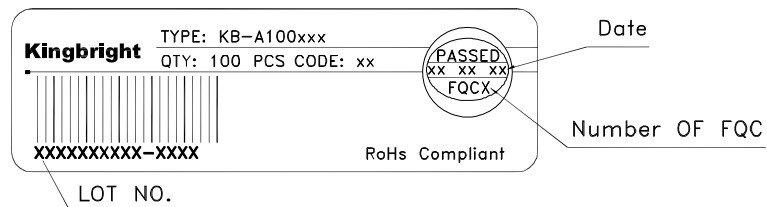


**PACKING & LABEL SPECIFICATIONS**

**KB-A100SURKW**



Inside Label On IC-tube



Outside Label On Box

